

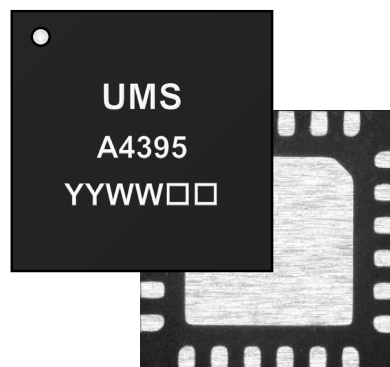
21-27GHz Medium Power Amplifier

GaAs Monolithic Microwave IC

Description

The CHA4395-QDG is a three-stage GaAs Medium Power Amplifier operating between 21GHz and 27GHz. This amplifier provides 23dBm maximum output power with 15% Power Added Efficiency and 21dBm Output Power at 1dB gain compression. The circuit exhibits a typical small signal gain of 22dB. This Medium Power Amplifier is well suited for a wide range of Telecom applications including RADAR and Space Communications.

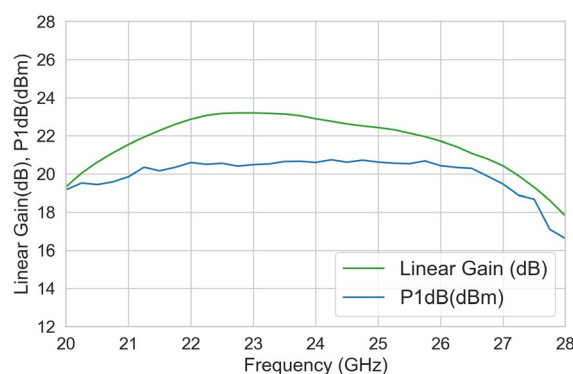
It is available in QFN plastic package. Input and output are 50Ω matched and integrate ESD RF protections.



Main Features

- Frequency range: 21-27GHz
- P1dB = 20dBm
- Linear Gain = 22dB
- ACPR < -35dBc @Pout = 17dBm⁽¹⁾
- EVM < 3.5% @Pout = 17dBm⁽¹⁾
- DC bias: Vd=4V@Id=230mA
- 24L-QFN 4x4mm²
- MSL1

⁽¹⁾ with 16QAM modulation, 150MHz & 300MHz bandwidth, Tcase = +25°C



Main Electrical Characteristics

Tcase = +25°C (Tcase : QFN backside temperature)

Symbol	Parameter	Min	Typ	Max	Unit
Freq	Frequency range	21		27	GHz
Gain	Linear Gain		22		dB
PAE	Power Added Efficiency		15		%
P1dB	Output Power @1dB comp.		21		dBm

Electrical Characteristics

$T_{case} = +25^{\circ}\text{C}$, $V_d = +4\text{V}$, (T_{case} : QFN backside temperature)

Symbol	Parameter	Min	Typ	Max	Unit
Freq	Frequency range	21		27	GHz
Gain	Linear Gain		22		dB
S_{11}	Input Return Loss		-12		dB
S_{22}	Output Return Loss		-10		dB
P1dB	Output Power @1dB Gain compression		21		dBm
NF	Noise Figure		4		dB
ACPR	ACPR @Pout = 17dBm with 16QAM modulation (BW = 150MHz, $\alpha = 0.22$)		-35		dBc
PAE	Power Added Efficiency @Pin = 2dBm		15		%
Idq	Quiescent Drain Current		230		mA

Absolute Maximum Ratings ⁽¹⁾

$T_{case} = +25^{\circ}\text{C}$

Symbol	Parameter	Values	Unit
Vd	Drain bias voltage	4.5	V
Idq	Maximum Quiescent Drain current	280	mA
Vg	Gate bias voltage	-1.5 to +0.4	V
Pin	Maximum peak input power overdrive	+4	dBm
Tj	Junction temperature	175	$^{\circ}\text{C}$

⁽¹⁾ Operation of this device above any one of these parameters may cause permanent damage.

Recommended Operating Range ⁽²⁾

Symbol	Parameter	Values	Unit
Vd	Drain bias voltage	3 to 4	V
Idq	Quiescent drain current	170 to 230	mA
Vg	Gate bias voltage	-1.5 to -0.7	V
Pin	Maximum peak input power overdrive ⁽²⁾	+3	dBm
T_{case}	Operating temperature range	-40 to +85	$^{\circ}\text{C}$
Tstg	Storage temperature range	-55 to +150	$^{\circ}\text{C}$

⁽²⁾ Electrical performances are defined for specified test conditions

Typical Bias Conditions $T_{\text{case}} = +25^{\circ}\text{C}$

Symbol	Parameter	Value	Unit
VG1, VG2, VG3	Gate voltage tuned for $I_{\text{dq}} = 230\text{mA}$	-0.3	V
VD1, VD2, VD3	Drain voltage	4	V

“Power ON” sequence

1. Ground the device
2. Set the gate voltage to -1.5V
3. Apply the drain voltage V_{d} (typically +4V)
4. Increase V_{g} up to quiescent drain current I_{dq}
5. Apply RF signal

“Power OFF” sequence

1. Turn off RF signal
2. Decrease the gate voltage to -1.5V
3. Decrease the drain voltage to 0V
4. Decrease the gate voltage to 0V
5. Turn off V_{d} supply
6. Turn off V_{g} supply

Device thermal performances

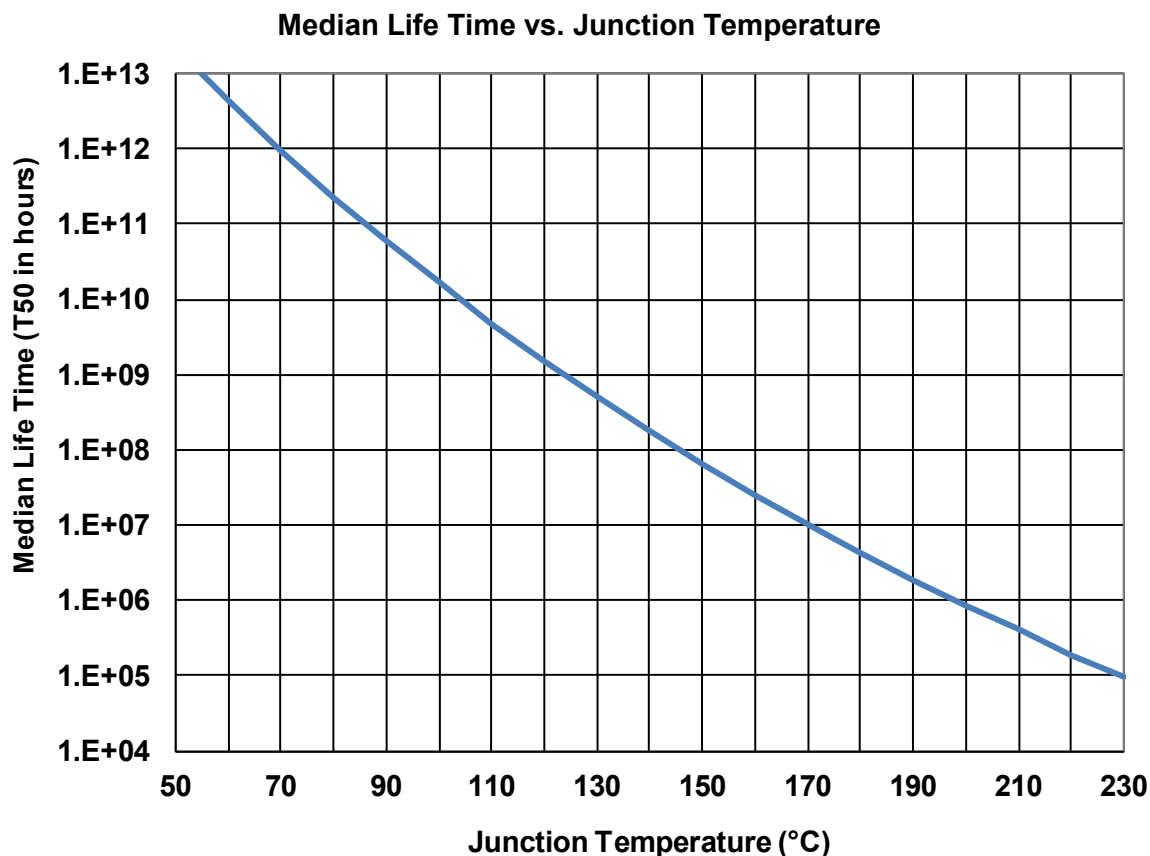
All figures provided in this section are based on the assumption that the QFN device is cooled solely by conduction through the package thermal pad, with no consideration of convection mode.

The temperature is monitored at the package backside interface (T_{case}).

For nominal operation, the system maximum temperature must be adjusted in order to guarantee that the junction temperature ($T_{junction}$) remains below the maximum value specified in the Absolute Maximum Ratings table. So the system PCB must be designed to comply with this requirement.

Parameter	Biasing conditions	$T_{JUNCTION}$ (°C)	R_{TH} (°C/W)	T50 (hours)
$R_{TH}^{(1)}$ Thermal Resistance (Junction to QFN Backside)	Vd=4V Pout=22dBm Pdis=0.85W	165	95	2E+7
	Vd=4V Small Signal Pdis=0.9W	170	95	1E+7

⁽¹⁾ Assuming 85°C T_{case}

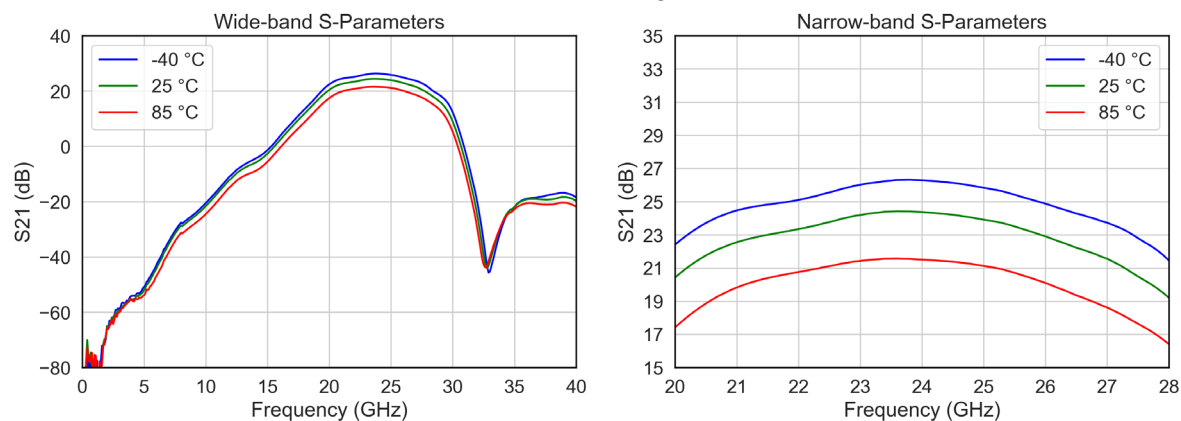


Typical S-Parameters Board Measurements

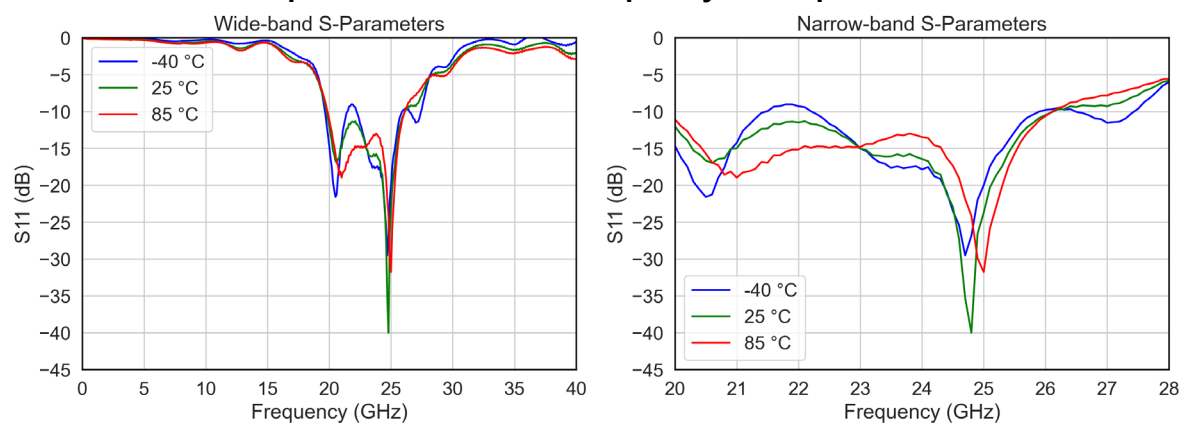
Test conditions : CW, $V_d = +4V$, $I_{dq} = 230mA$, $T_{case} = -40^{\circ}C/25^{\circ}C/85^{\circ}C$

Measurements are given in QFN access planes.

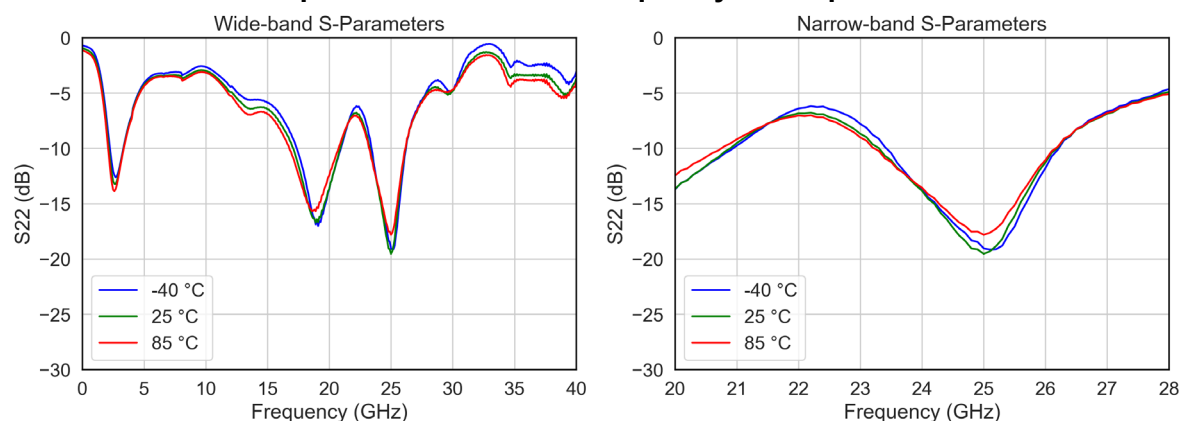
Linear Gain vs. Frequency & Temperature



Input Return Loss vs. Frequency & Temperature



Output Return Loss vs. Frequency & Temperature

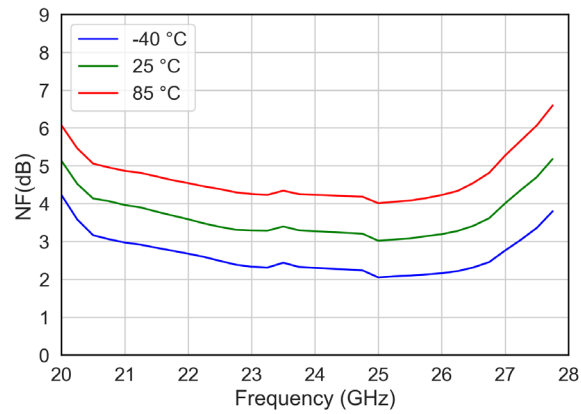


Typical Board Measurements : Noise Figure

Test conditions : CW, $V_d = +4V$, $I_{dq} = 230mA$, $T_{case} = -40^{\circ}C/25^{\circ}C/85^{\circ}C$

Measurements are given in QFN access planes.

Noise Figure vs. Frequency & Temperature

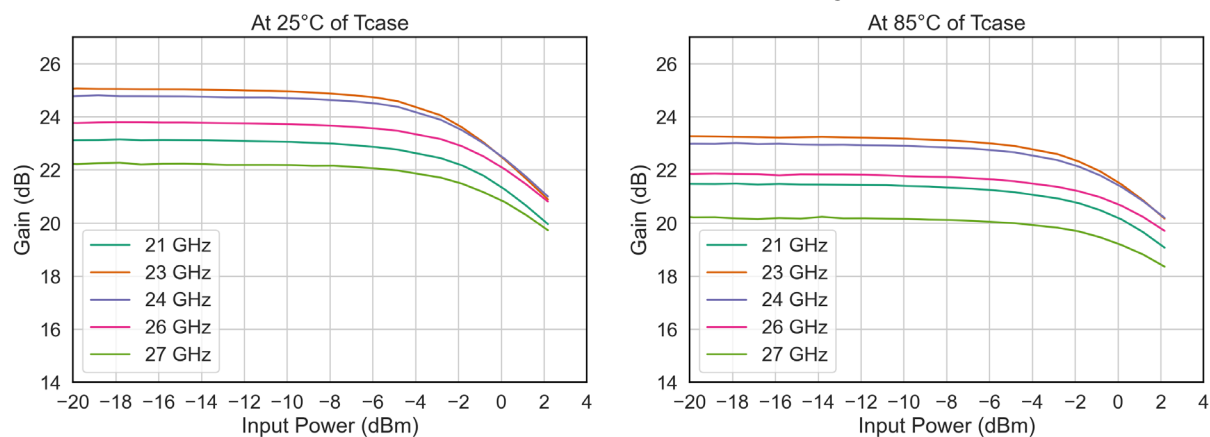


Typical CW Board Measurements vs. Input Power

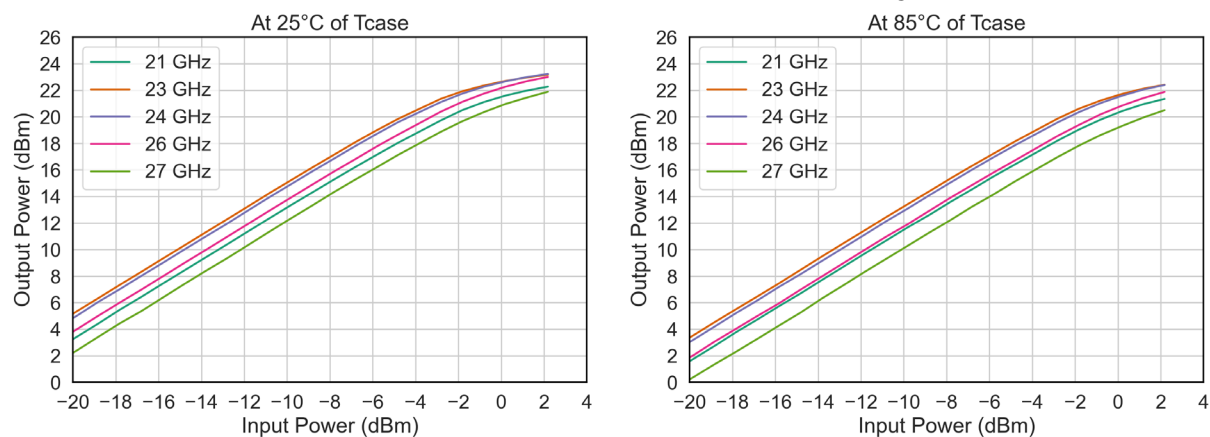
Test conditions : CW, $V_d = +4V$, $I_{dq} = 230mA$, $T_{case} = +25^{\circ}C/85^{\circ}C$

Measurements are given in the QFN access planes.

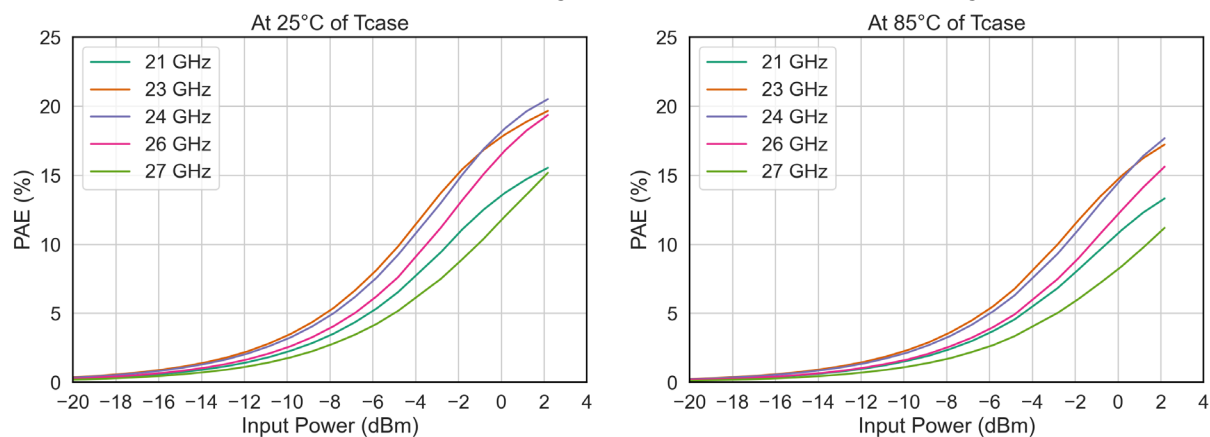
Gain vs. Input Power & Frequency



Output Power vs. Input Power & Frequency



Power Added Efficiency vs. Input Power & Frequency

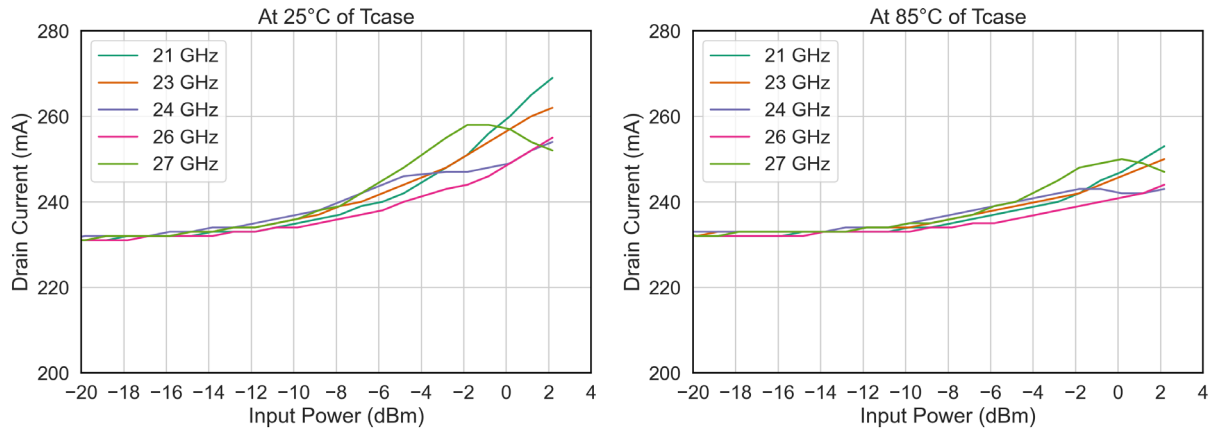


Typical CW Board Measurements vs. Input Power

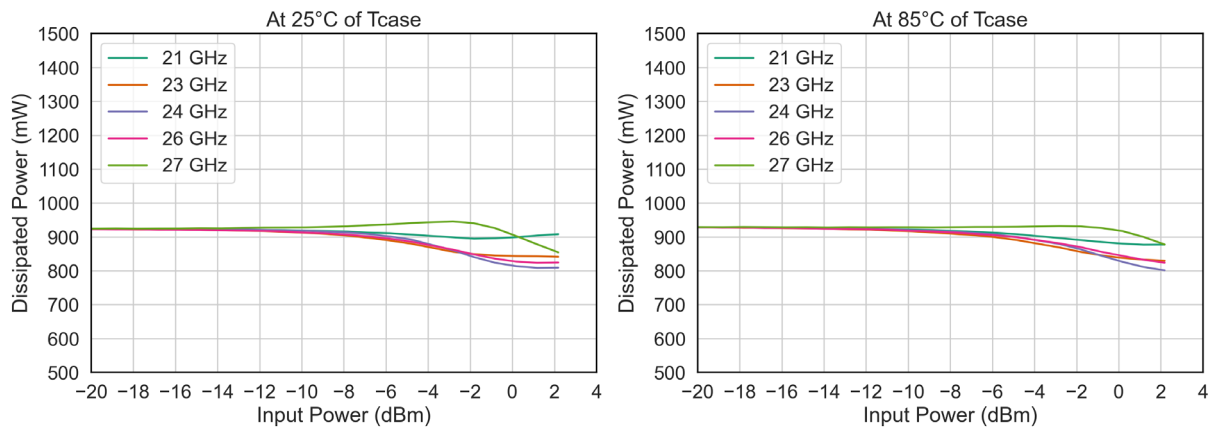
Test conditions : CW, $V_d = +4V$, $I_{dq} = 230mA$, $T_{case} = +25^{\circ}C/85^{\circ}C$

Measurements are given in the QFN access planes.

Drain Current vs. Input Power & Frequency



Dissipated Power vs. Input Power & Frequency

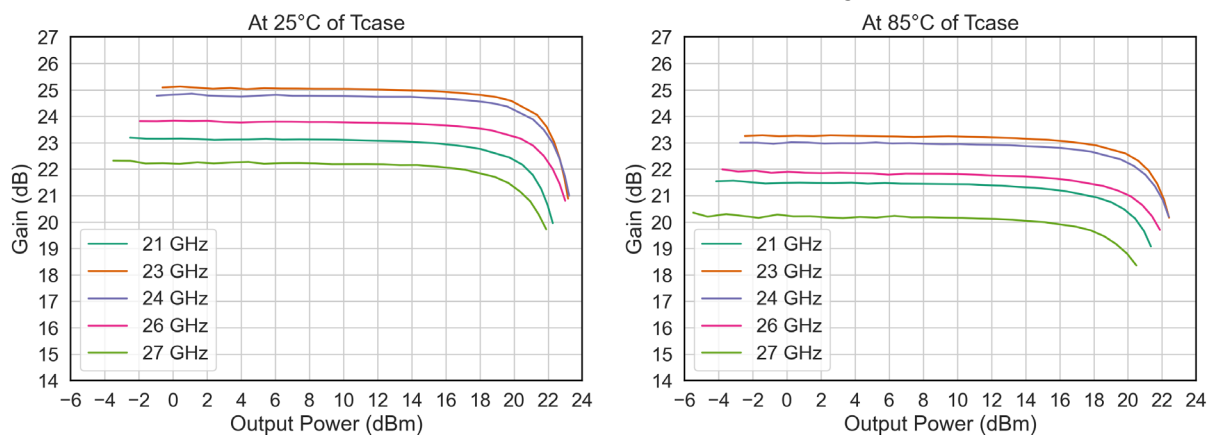


Typical CW Board Measurements vs. Output Power

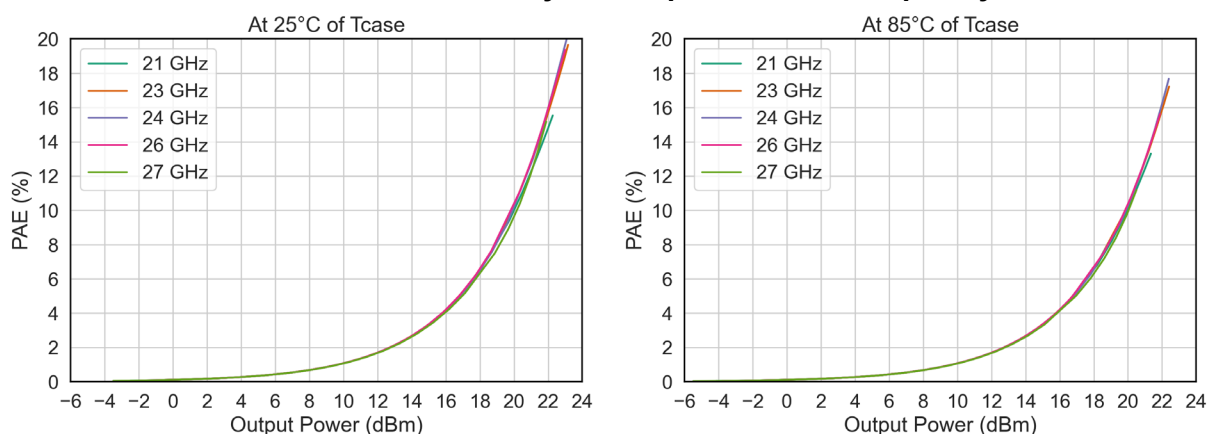
Test conditions : CW, $V_d = +4V$, $I_{dq} = 230mA$, $T_{case} = +25^{\circ}C/85^{\circ}C$

Measurements are given in the QFN access planes.

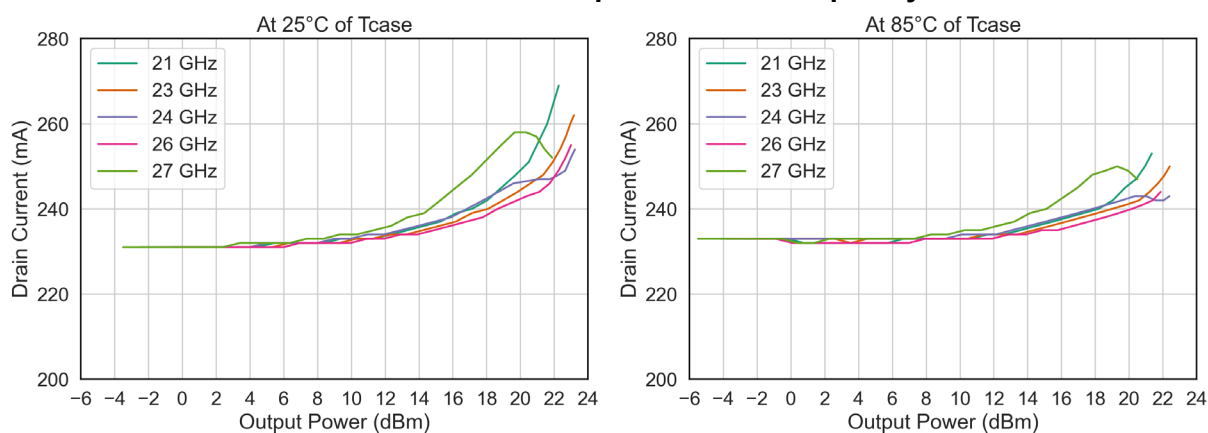
Gain vs. Output Power & Frequency



Power Added Efficiency vs. Output Power & Frequency



Drain Current vs. Output Power & Frequency

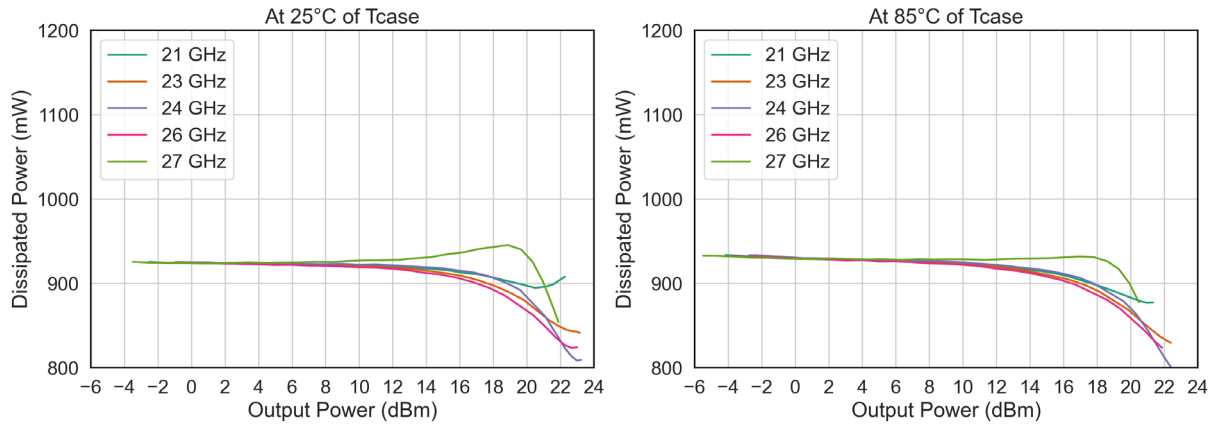


Typical CW Board Measurements vs. Output Power

Test conditions : CW, $V_d = +4V$, $I_{dq} = 230mA$, $T_{case} = +25^{\circ}C/85^{\circ}C$

Measurements are given in the QFN access planes.

Dissipated Power vs. Output Power & Frequency

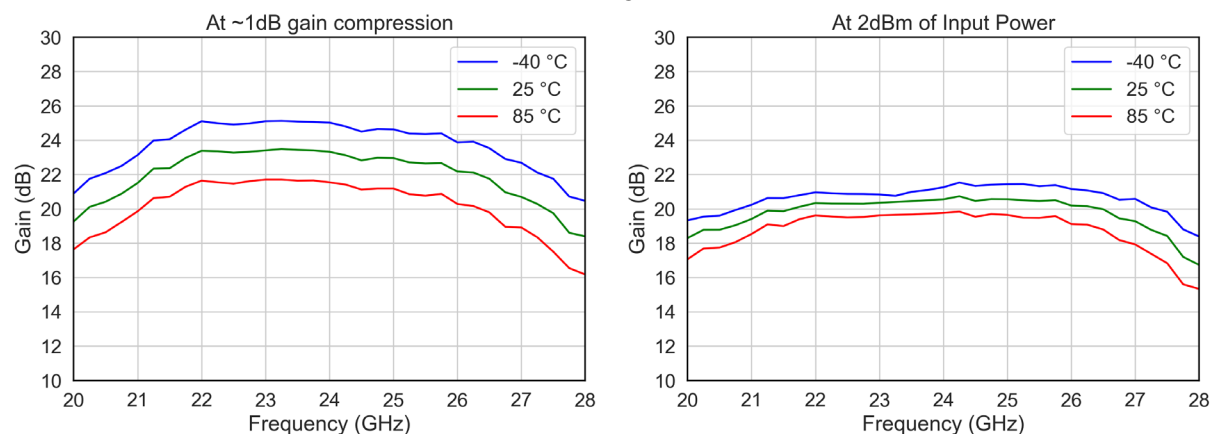


Typical CW Board Measurements vs. Frequency

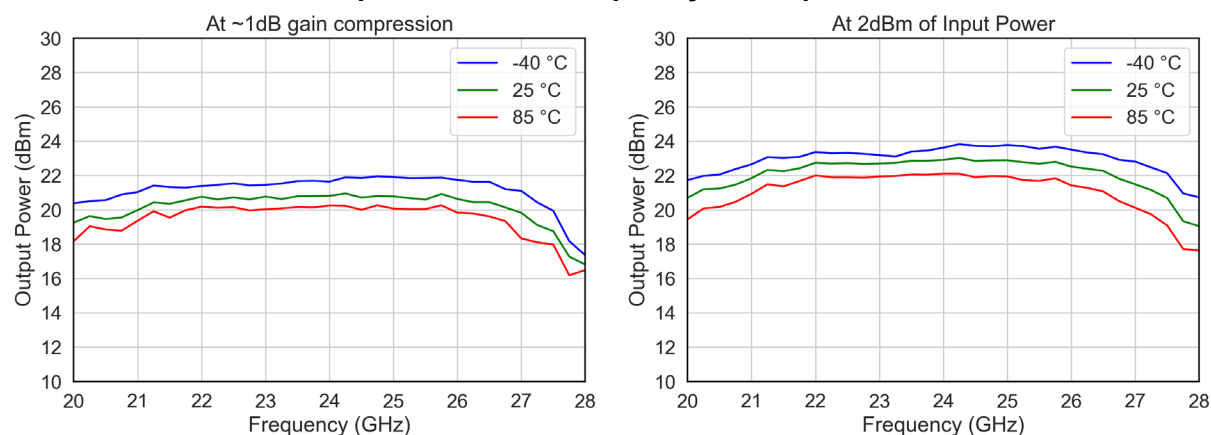
Test conditions : CW, $V_d = +4V$, $I_{dq} = 230mA$, $T_{case} = -40^{\circ}C/25^{\circ}C/85^{\circ}C$

Measurements are given in the QFN access planes

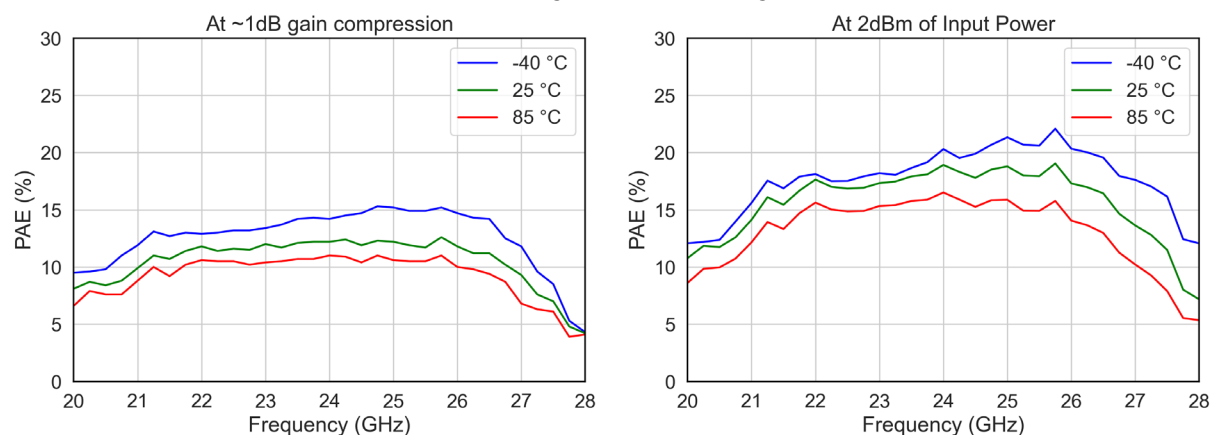
Gain vs. Frequency & Temperature



Output Power vs. Frequency & Temperature



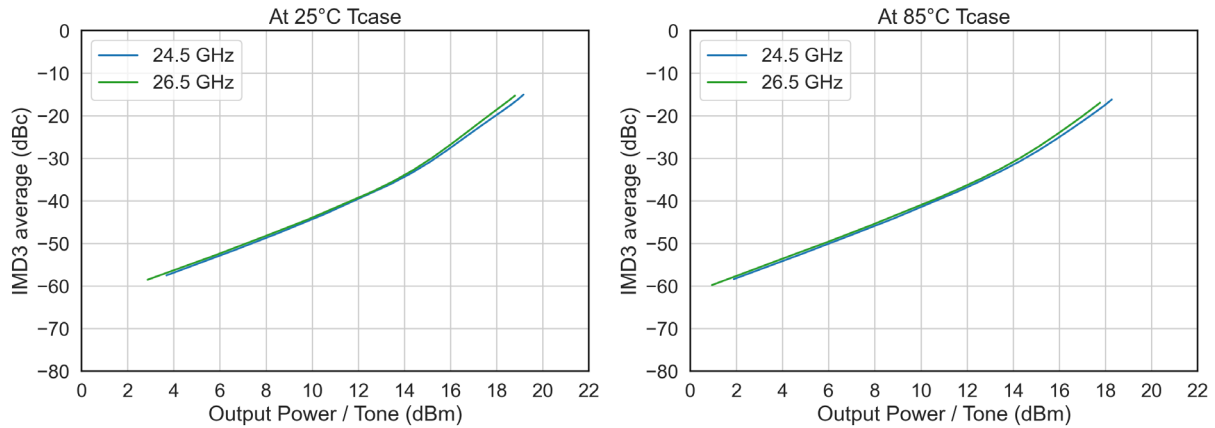
Power Added Efficiency vs. Frequency & Temperature



Typical Board Measurements : Modulation Results

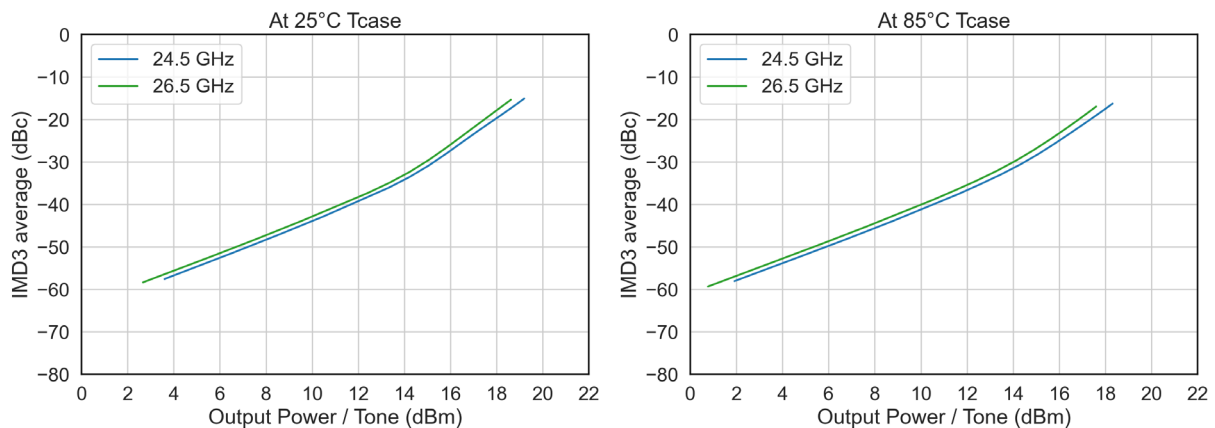
Test conditions : CW dual tones, $V_d = +4V$, $I_{dq} = 230mA$, $\Delta f = 10MHz$, $T_{case} = +25^{\circ}C/85^{\circ}C$

IMD3 vs. Output Power per Tone & Frequency



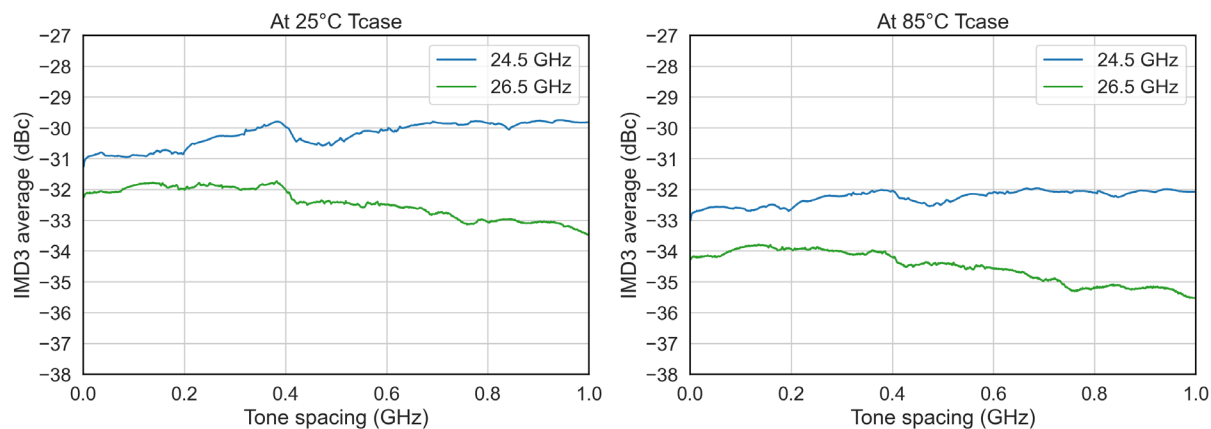
Test conditions : CW dual tones, $V_d = +4V$, $I_{dq} = 230mA$, $\Delta f = 100MHz$, $T_{case} = +25^{\circ}C/85^{\circ}C$

IMD3 vs. Output Power per Tone & Frequency

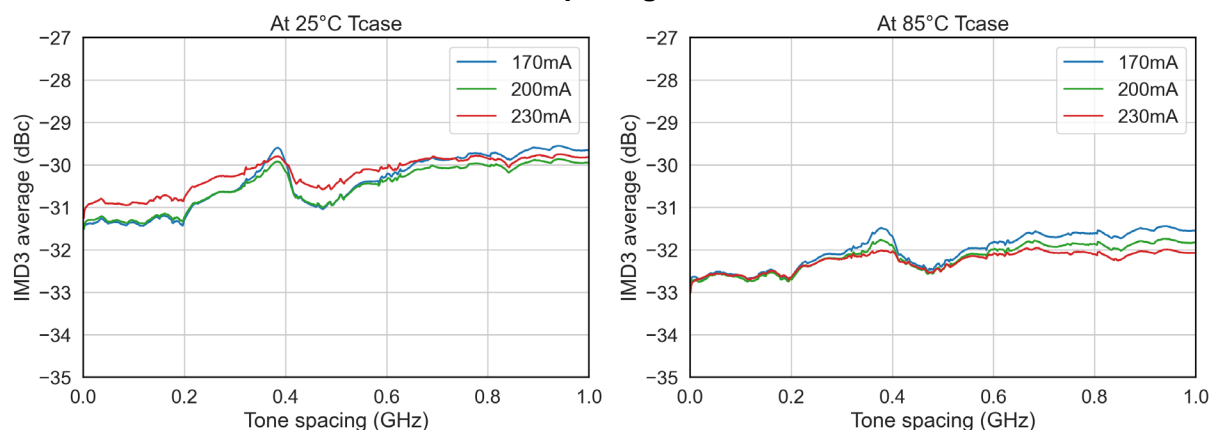


Typical Board Measurements : Modulation Results

Test conditions : CW dual tones, $V_d = +4V$, $I_{dq} = 230mA$, $P_{out} = 17dBm$, $T_{case} = +25^{\circ}C/85^{\circ}C$

IMD3 vs. Tone Spacing & Frequency

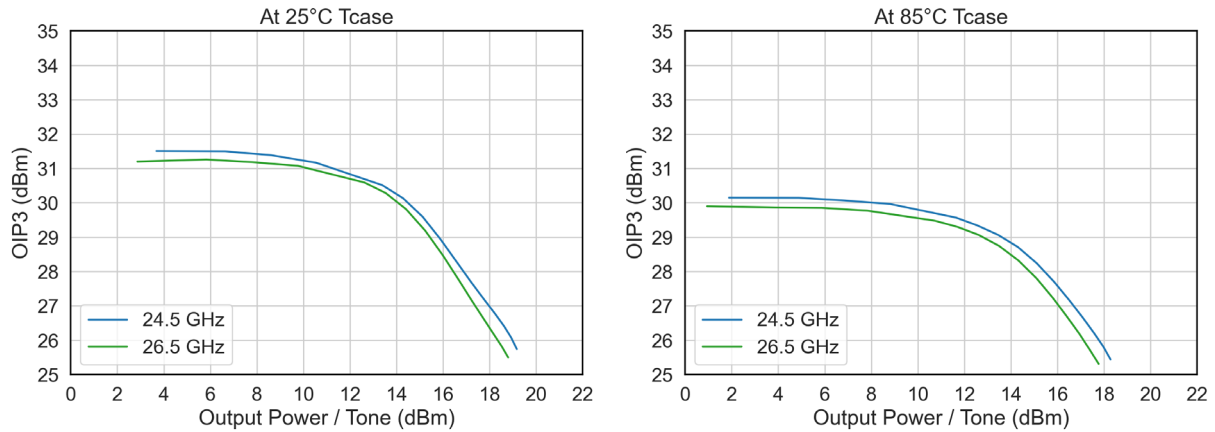
Test conditions : CW dual tones, $V_d = +4V$, $F_c = 24.5GHz$, $P_{out} = 17dBm$, $T_{case} = +25^{\circ}C/85^{\circ}C$

IMD3 vs. Tone Spacing & Drain Current

Typical Board Measurements : Modulation Results

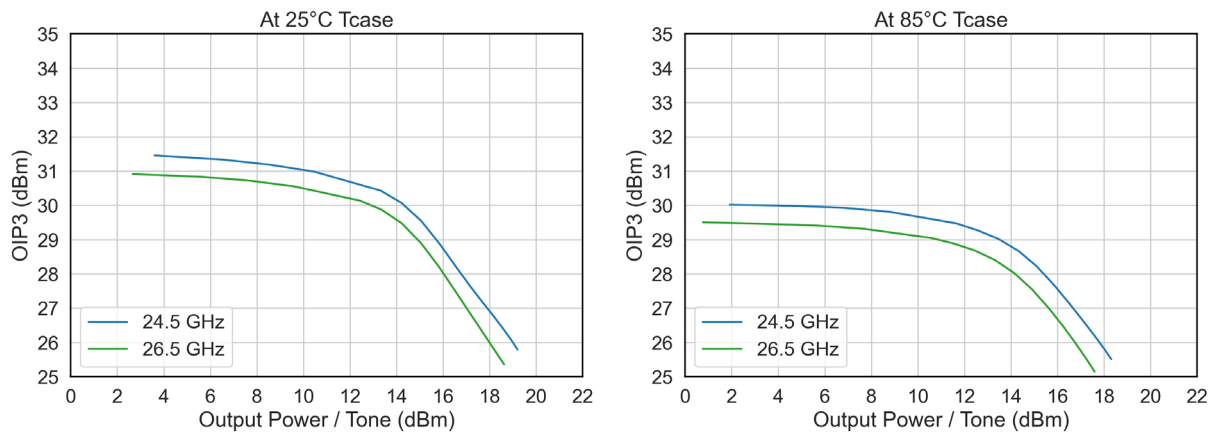
Test conditions : CW dual tones, $V_d = +4V$, $I_{dq} = 230mA$, $\Delta f = 10MHz$, $T_{case} = +25^\circ C/85^\circ C$

OIP3 vs. Output Power per Tone & Central Frequency



Test conditions : CW dual tones, $V_d = +4V$, $I_{dq} = 230mA$, $\Delta f = 100MHz$, $T_{case} = +25^\circ C/85^\circ C$

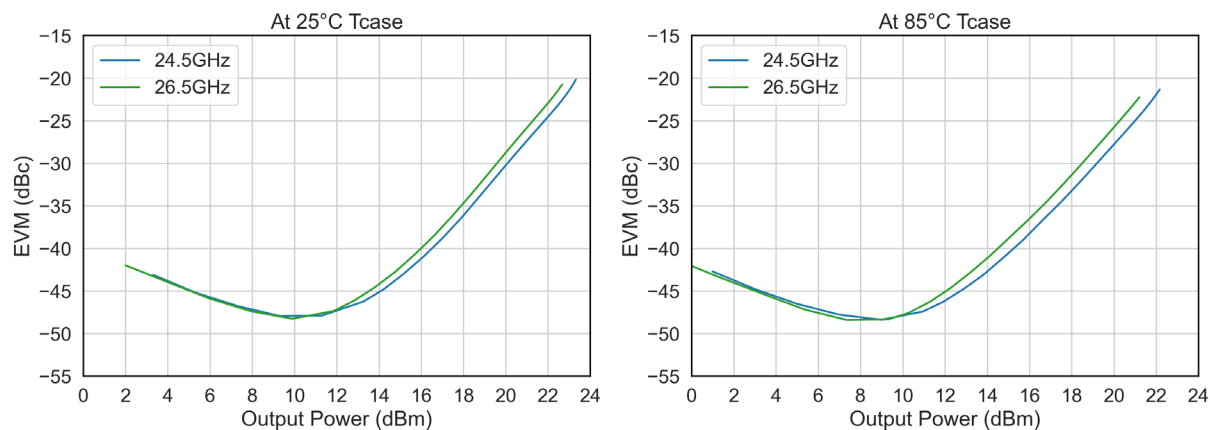
OIP3 vs. Output Power per Tone & Frequency



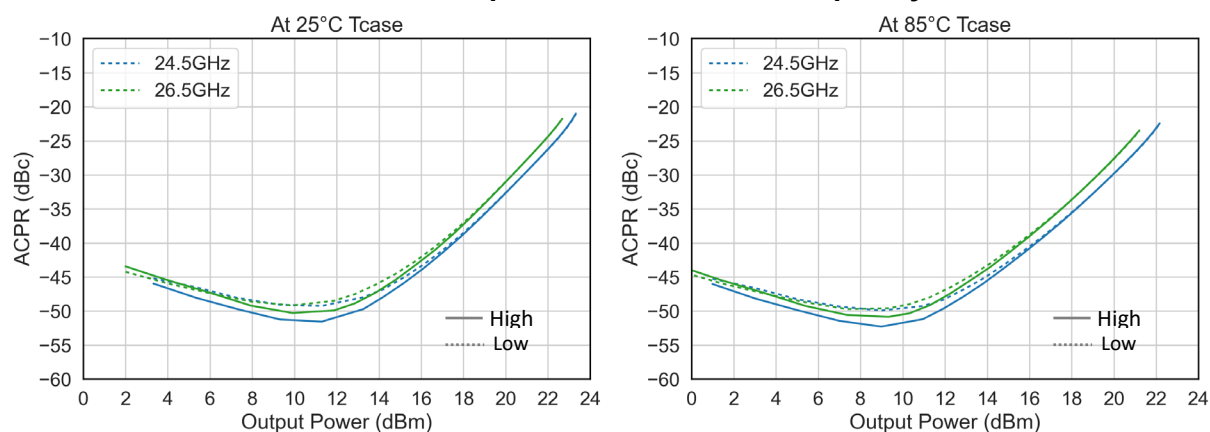
Typical Board Measurements : Modulation Results

Test conditions : $V_d = +4V$, $I_{dq} = 230mA$, **8PSK**, **BW = 150MHz**, Roll-off = 0.2, PAPR = 5.1dB, $T_{case} = +25^{\circ}C/85^{\circ}C$

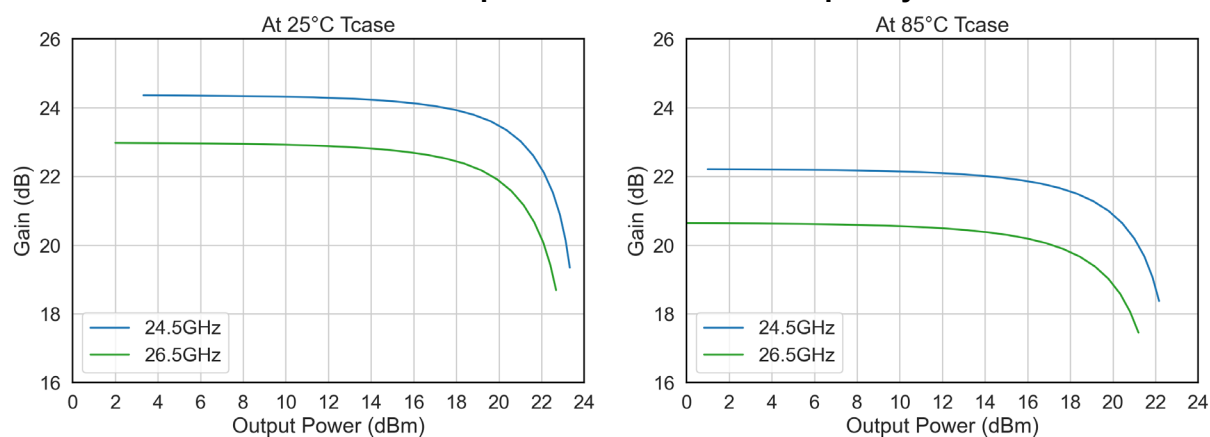
EVM vs. Output Power & Central Frequency



ACPR vs. Output Power & Central Frequency



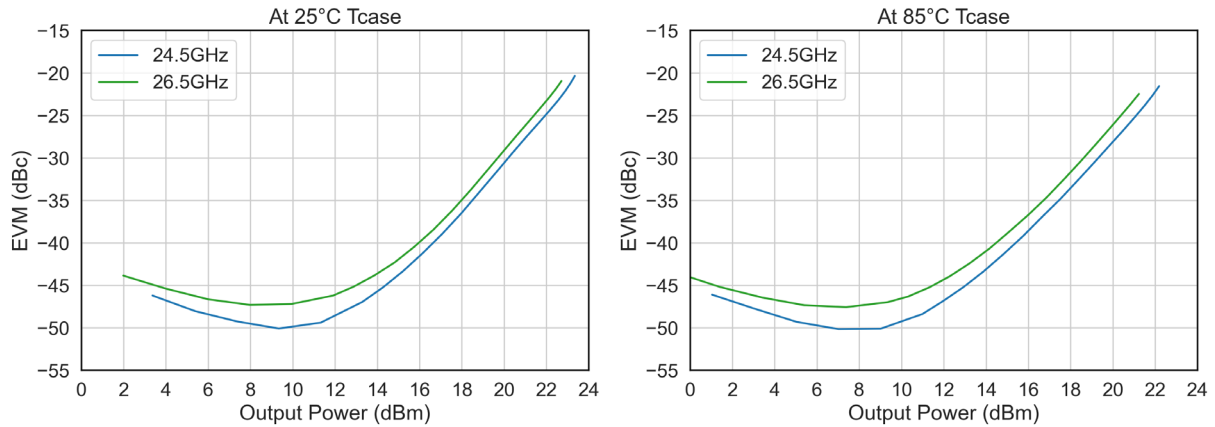
Gain vs. Output Power & Central Frequency



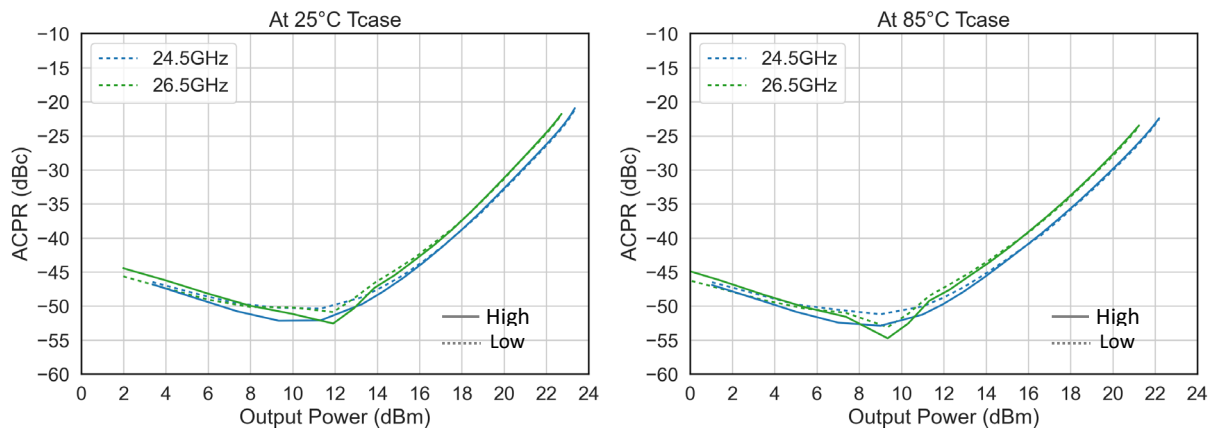
Typical Board Measurements : Modulation Results

Test conditions : $V_d = +4V$, $I_{dq} = 230mA$, **8PSK**, **BW = 300MHz**, Roll-off = 0.2, PAPR = 5.1dB, $T_{case} = +25^{\circ}C/85^{\circ}C$

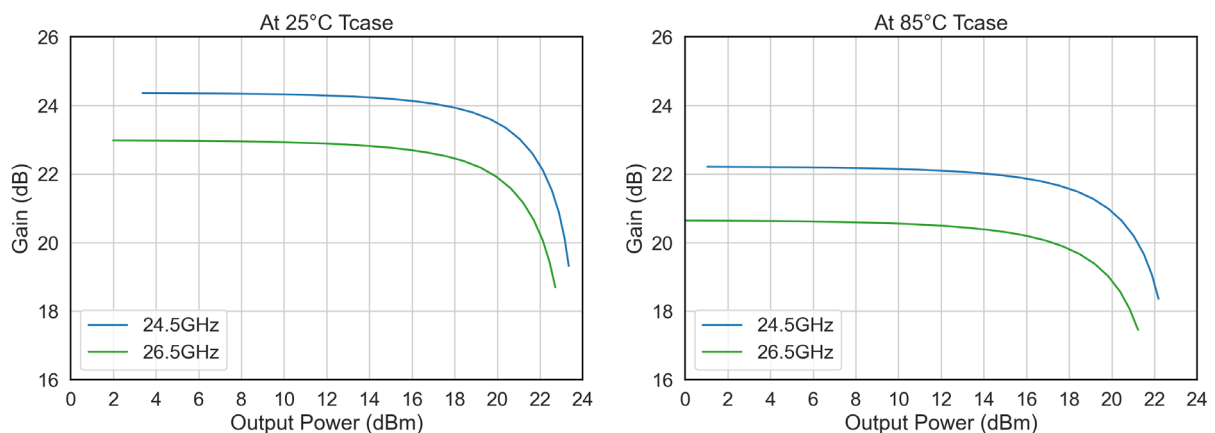
EVM vs. Output Power & Central Frequency



ACPR vs. Output Power & Central Frequency



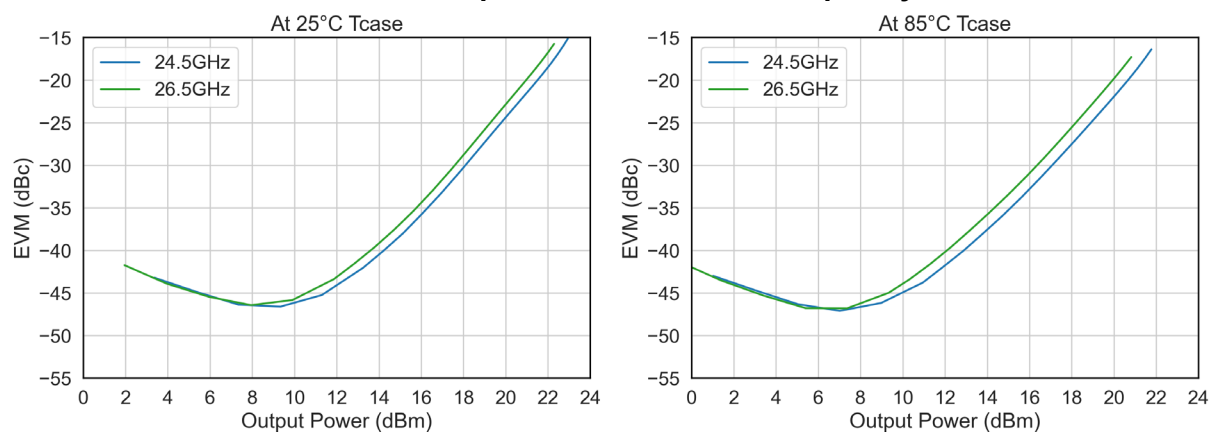
Gain vs. Output Power & Central Frequency



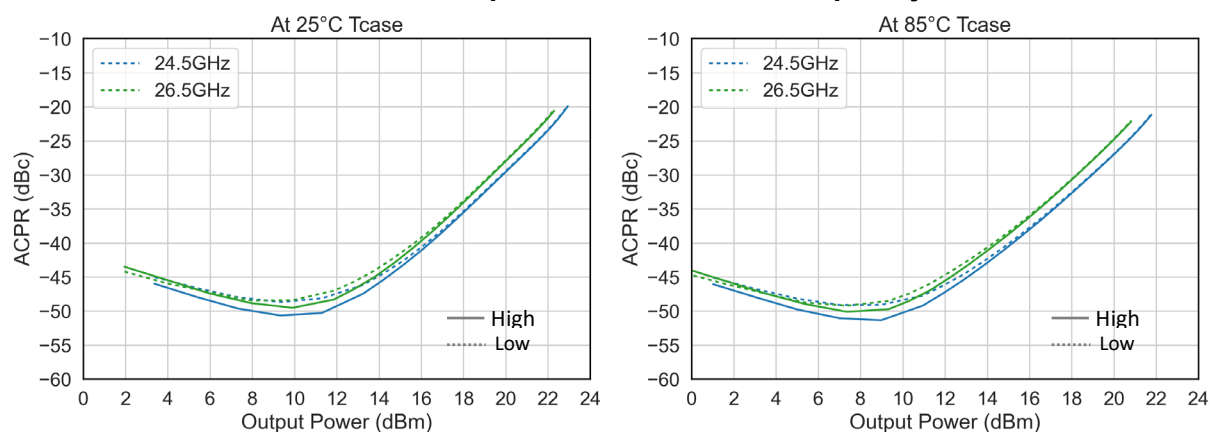
Typical Board Measurements : Modulation Results

Test conditions : $V_d = +4V$, $I_{dq} = 230mA$, **16QAM**, **BW = 150MHz**, Roll-off = 0.2, PAPR = 6.5dB, $T_{case} = +25^{\circ}C/85^{\circ}C$

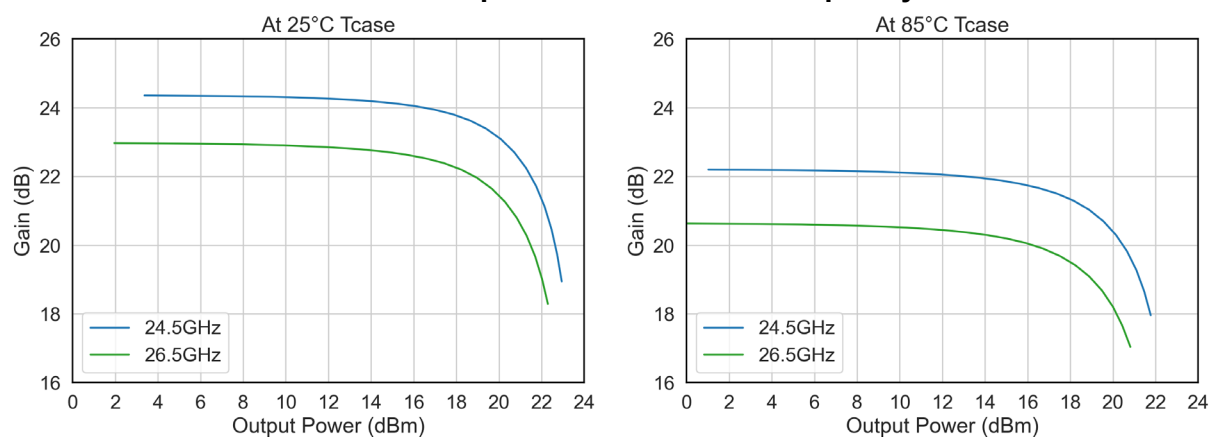
EVM vs. Output Power & Central Frequency



ACPR vs. Output Power & Central Frequency



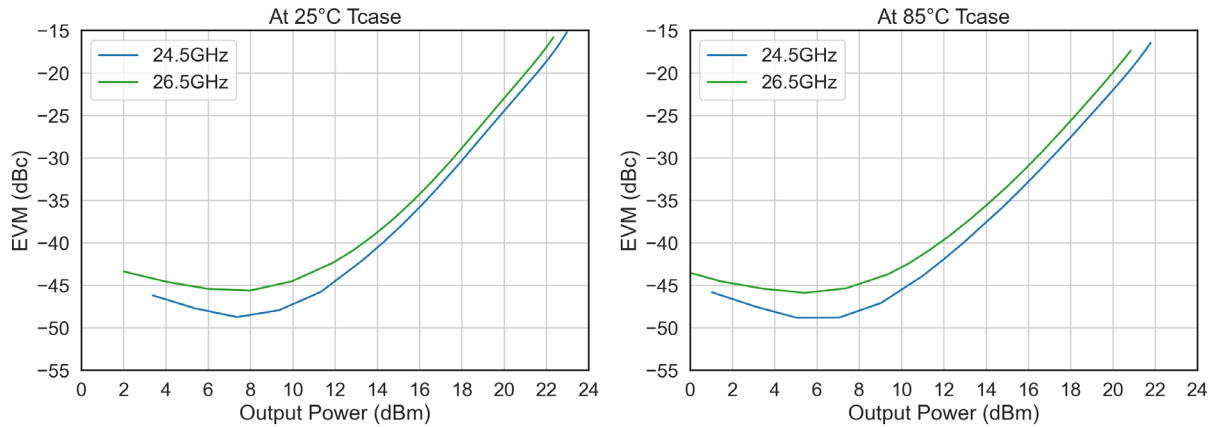
Gain vs. Output Power & Central Frequency



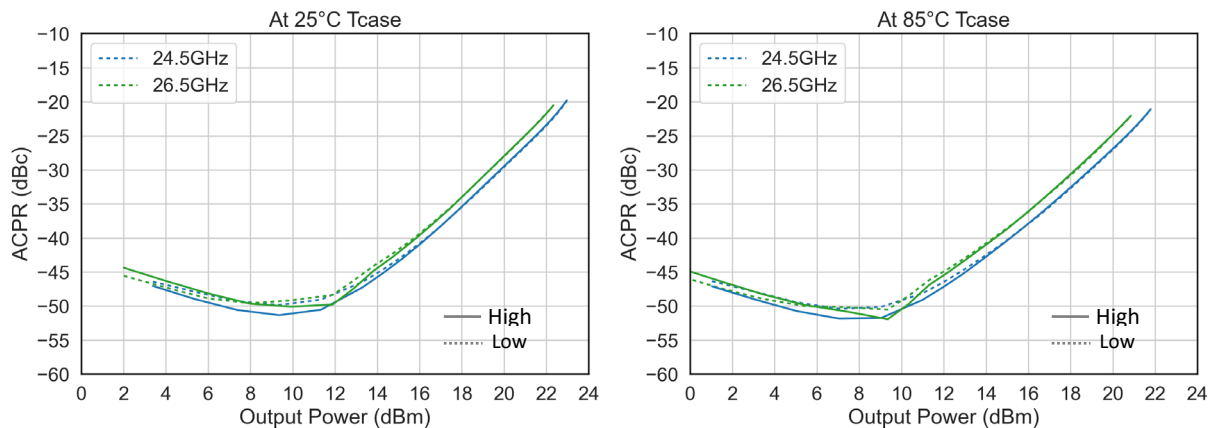
Typical Board Measurements : Modulation Results

Test conditions : $V_d = +4V$, $I_{dq} = 230mA$, **16QAM**, **BW = 300MHz**, Roll-off = 0.2, PAPR = 6.5dB, $T_{case} = +25^{\circ}C/85^{\circ}C$

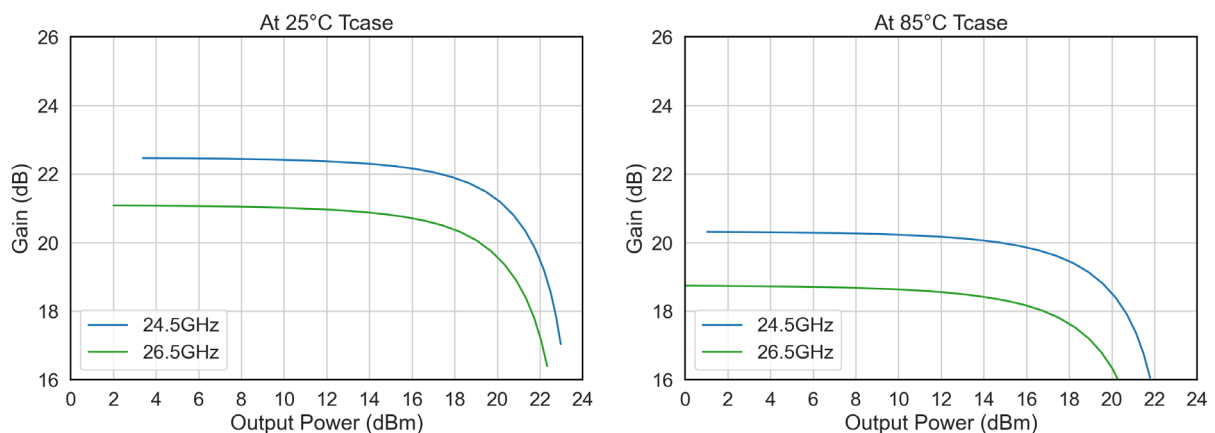
EVM vs. Output Power & Central Frequency



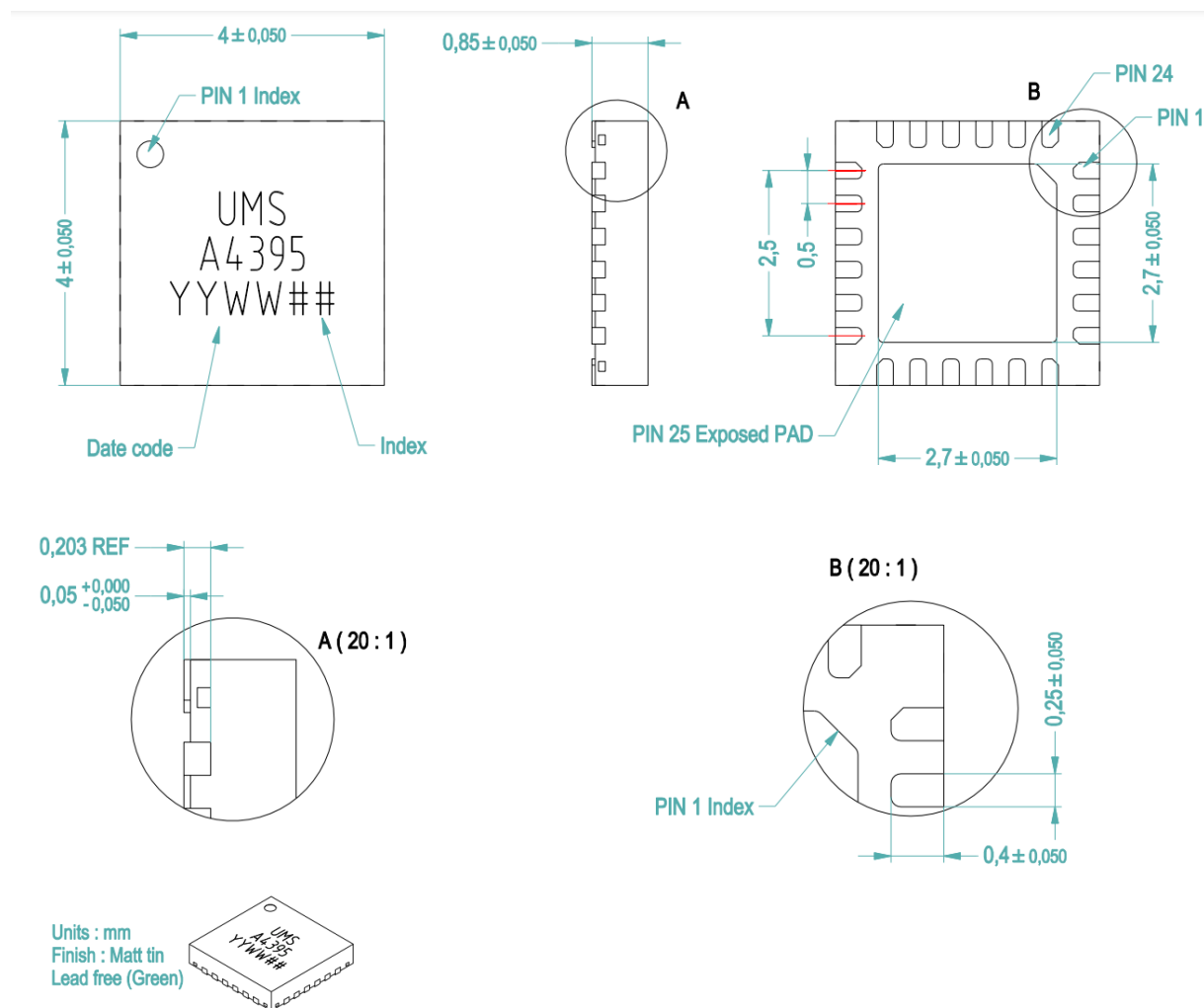
ACPR vs. Output Power & Central Frequency



Gain vs. Output Power & Central Frequency



Package outline

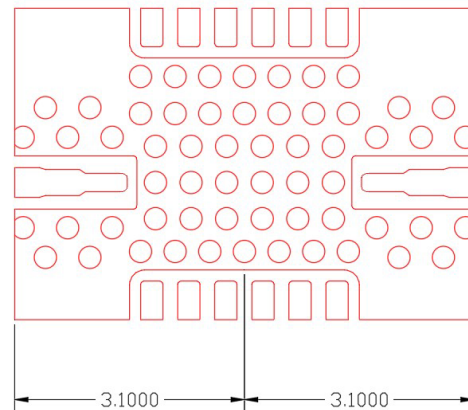


Finish:	Matt Tin Lead Free (Green)	1- NC	11- GND ⁽¹⁾	21- VD3
Units :	mm	2- GND ⁽¹⁾	12- NC	22- VD2
From the standard :	JEDEC MO-220	3- GND ⁽¹⁾	13- GND ⁽¹⁾	23- VD1
	(VGGD)	4- RFin	14- GND ⁽¹⁾	24- NC
NC :	Not Connected	5- GND ⁽¹⁾	15- RFout	25- GND ⁽¹⁾
		6- GND ⁽¹⁾	16- GND ⁽¹⁾	
		7- NC	17- GND ⁽¹⁾	
		8- VG1	18- NC	
		9- VG2	19- NC	
		10- VG3	20- GND ⁽¹⁾	

⁽¹⁾ It is strongly recommended to ground all pins marked "GND" through the PCB. Ensure that the PCB board is designed to provide the best possible ground to the package.

Definition of measurement reference planes

Reference planes used for measurements given above are symmetrical from the central axis of the package (see drawing beside). Input and output reference planes are located at 3.1mm offset (input wise and output wise respectively) from this axis.



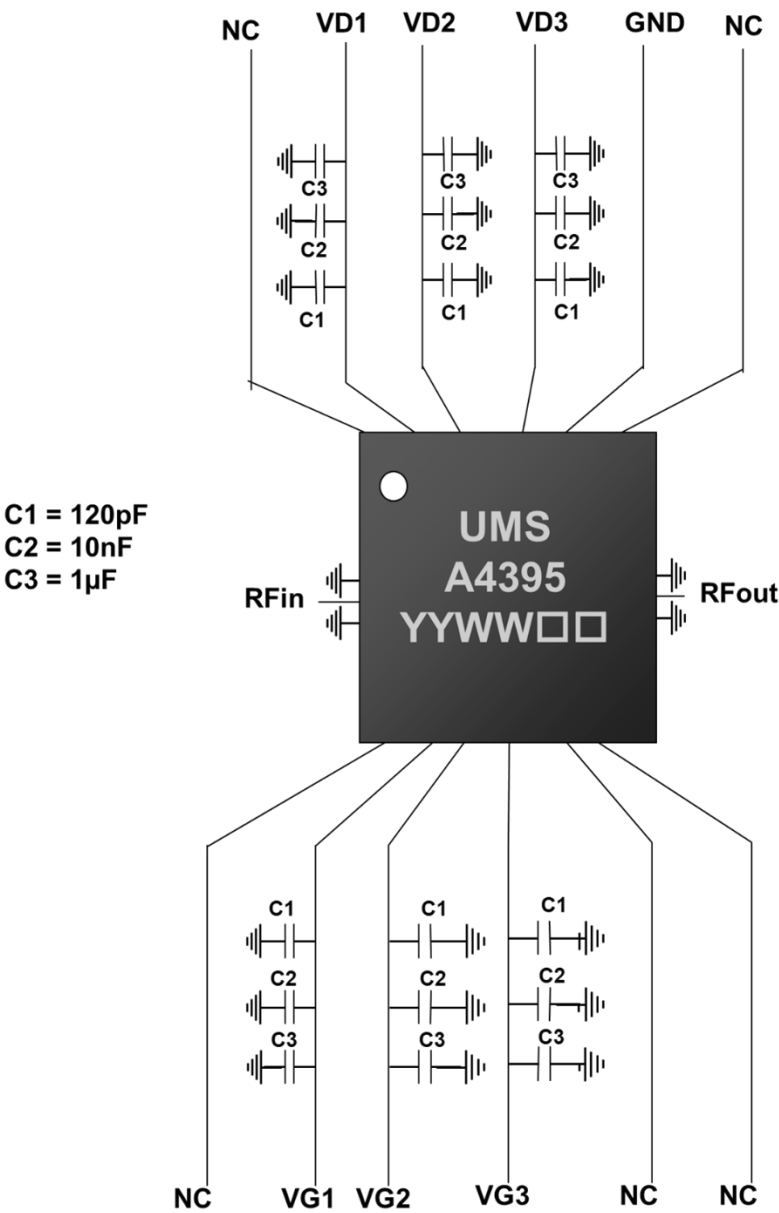
ESD sensitivity

Parameter	Classification	Standard
Human Body Model (HBM)	1A	JESD22 A114
Charge Device Model (CDM)	III	JESD22 A101

Package Information

Parameter	Value
Package body material	RoHS-compliant
	Low stress Injection Molded Plastic
Lead finish	100% Matt Tin
Moisture Sensitivity Level	MSL1

Recommended assembly plan

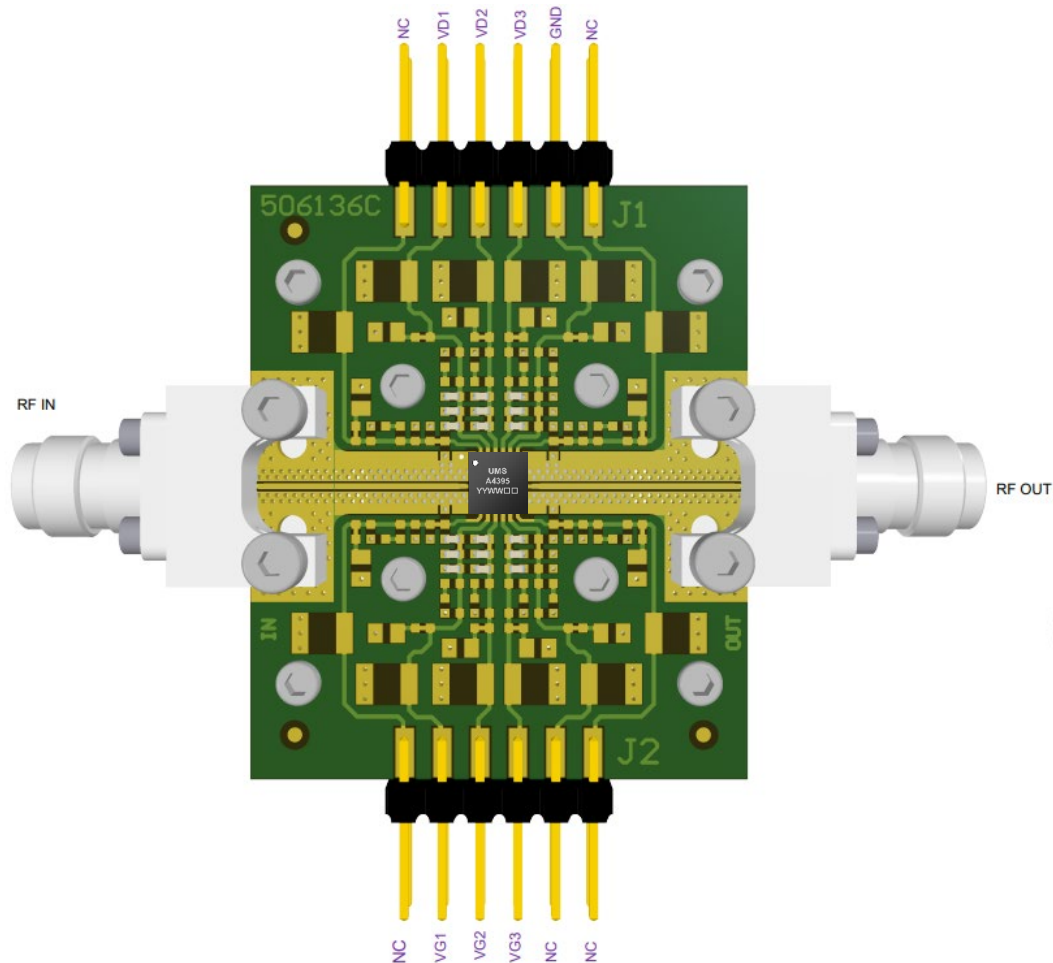


Recommended circuit bonding table

Label	Pin	Type	Decoupling	Comment
VD1, VD2, VD3	21, 22, 23	Vd	120pF, 10nF & 1μF	Drain Supply
VG1, VG2, VG3	8, 9, 10	Vg	120pF, 10nF & 1μF	Gate Supply

Evaluation board

- Compatible with the proposed footprint.
- Based on typically Ro4350B / 8mils or equivalent.
- Using a micro-strip to coplanar transition to access the package.
- Recommended for the implementation of this product on a module board.
- Decoupling capacitors of $120\text{pF} \pm 10\%$, $10\text{nF} \pm 10\%$ & $1\mu\text{F} \pm 10\%$ are recommended for all DC access.
- To ensure safe operation, all measurements must be performed using **shielded cables**, even for DC bias.



Notes

Due to ESD protection circuits on RF input and output, an external capacitance might be requested to isolate the product from external voltage that could be present on each RF access.

ESD protections are also implemented on gate and control access.

The DC connections do not include any decoupling capacitors in the package. Therefore it is mandatory to provide a good external DC decoupling (120pF, 10nF & 1µF) on the PC board as close as possible to the package.

Recommended package footprint

Refer to the application note AN0017 available at <https://www.ums-rf.com/> for package footprint recommendations.

SMD mounting procedure

For the mounting process standard techniques involving solder paste and a suitable reflow process can be used. For further details, see application note AN0017 available at <https://www.ums-rf.com/>.

Recommended environmental management

UMS products are compliant with the regulation in particular with the directives RoHS N°2011/65 and REACH N°1907/2006. More environmental data are available in the application note AN0019 also available at <https://www.ums-rf.com/>.

Recommended ESD management

Refer to the application note AN0020 available at <https://www.ums-rf.com/> for ESD sensitivity and handling recommendations for the UMS package products.

Description of Evaluation Board

Refer to the application note AN0031 available at <https://www.ums-rf.com/> for the description of Evaluation Board for Packaged Die and recommendations for this UMS package product.

Ordering request reference

QFN 4x4 package :	CHA4395-QDG/XY	
	Stick: XY = 20	Tape & reel: XY = 21
Evaluation board :	EVB-CHA4395-QDG	

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